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Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	55296
Number of I/O	151
Number of Gates	400000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	208-BFQFP
Supplier Device Package	208-PQFP (28x28)
Purchase URL	https://www.e-xfl.com/product-detail/microchip-technology/a3p400-2pqg208i

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong



User Nonvolatile FlashROM

ProASIC3 devices have 1 kbit of on-chip, user-accessible, nonvolatile FlashROM. The FlashROM can be used in diverse system applications:

- Internet protocol addressing (wireless or fixed)
- System calibration settings
- Device serialization and/or inventory control
- Subscription-based business models (for example, set-top boxes)
- Secure key storage for secure communications algorithms
- Asset management/tracking
- Date stamping
- Version management

The FlashROM is written using the standard ProASIC3 IEEE 1532 JTAG programming interface. The core can be individually programmed (erased and written), and on-chip AES decryption can be used selectively to securely load data over public networks (except in the A3P015 and A3P030 devices), as in security keys stored in the FlashROM for a user design.

The FlashROM can be programmed via the JTAG programming interface, and its contents can be read back either through the JTAG programming interface or via direct FPGA core addressing. Note that the FlashROM can only be programmed from the JTAG interface and cannot be programmed from the internal logic array.

The FlashROM is programmed as 8 banks of 128 bits; however, reading is performed on a byte-by-byte basis using a synchronous interface. A 7-bit address from the FPGA core defines which of the 8 banks and which of the 16 bytes within that bank are being read. The three most significant bits (MSBs) of the FlashROM address determine the bank, and the four least significant bits (LSBs) of the FlashROM address define the byte.

The ProASIC3 development software solutions, Libero[®] System-on-Chip (SoC) and Designer, have extensive support for the FlashROM. One such feature is auto-generation of sequential programming files for applications requiring a unique serial number in each part. Another feature allows the inclusion of static data for system version control. Data for the FlashROM can be generated quickly and easily using Libero SoC and Designer software tools. Comprehensive programming file support is also included to allow for easy programming of large numbers of parts with differing FlashROM contents.

SRAM and FIFO

ProASIC3 devices (except the A3P015 and A3P030 devices) have embedded SRAM blocks along their north and south sides. Each variable-aspect-ratio SRAM block is 4,608 bits in size. Available memory configurations are 256×18, 512×9, 1k×4, 2k×2, and 4k×1 bits. The individual blocks have independent read and write ports that can be configured with different bit widths on each port. For example, data can be sent through a 4-bit port and read as a single bitstream. The embedded SRAM blocks can be initialized via the device JTAG port (ROM emulation mode) using the UJTAG macro (except in A3P015 and A3P030 devices).

In addition, every SRAM block has an embedded FIFO control unit. The control unit allows the SRAM block to be configured as a synchronous FIFO without using additional core VersaTiles. The FIFO width and depth are programmable. The FIFO also features programmable Almost Empty (AEMPTY) and Almost Full (AFULL) flags in addition to the normal Empty and Full flags. The embedded FIFO control unit contains the counters necessary for generation of the read and write address pointers. The embedded SRAM/FIFO blocks can be cascaded to create larger configurations.

PLL and CCC

ProASIC3 devices provide designers with very flexible clock conditioning capabilities. Each member of the ProASIC3 family contains six CCCs. One CCC (center west side) has a PLL. The A3P015 and A3P030 devices do not have a PLL.

The six CCC blocks are located at the four corners and the centers of the east and west sides.

All six CCC blocks are usable; the four corner CCCs and the east CCC allow simple clock delay operations as well as clock spine access.

The inputs of the six CCC blocks are accessible from the FPGA core or from one of several inputs located near the CCC that have dedicated connections to the CCC block.



0-I/O is set to drive out logic Low

Last Known State – I/O is set to the last value that was driven out prior to entering the programming mode, and then held at that value during programming

Z -Tristate: I/O is tristated

rom file Save to file			Show BSR De
Port Name	Macro Cell	Pin Number	1/O State (Output Only)
BIST	ADLIB:INBUF	T2	1
BYPASS_IO	ADLIB:INBUF	K1	1
CLK	ADLIB:INBUF	B1	1
ENOUT	ADLIB:INBUF	J16	1
LED	ADLIB:OUTBUF	M3	0
MONITOR(0)	ADLIB:OUTBUF	B5	0
MONITOR[1]	ADLIB:OUTBUF	C7	Z
MONITOR[2]	ADLIB:OUTBUF	D9	Z
MONITOR(3)	ADLIB:OUTBUF	D7	Z
MONITOR[4]	ADLIB:OUTBUF	A11	Z
OEa	ADLIB:INBUF	E4	Z
ОЕЬ	ADLIB:INBUF	F1	Z
OSC_EN	ADLIB:INBUF	K3	Z
PAD[10]	ADLIB:BIBUF_LVCMOS33U	M8	Z
PAD[11]	ADLIB:BIBUF_LVCMOS33D	R7	Z
PAD[12]	ADLIB:BIBUF_LVCMOS33U	D11	Z
PAD[13]	ADLIB:BIBUF_LVCMOS33D	C12	Z
PAD[14]	ADLIB:BIBUF_LVCMOS33U	R6	Z
1			-

Figure 1-4 • I/O States During Programming Window

- 6. Click OK to return to the FlashPoint Programming File Generator window.
- Note: I/O States During programming are saved to the ADB and resulting programming files after completing programming file generation.



Table 2-2 • Recommended Operating Conditions¹

Symbol	Parame	eters ¹	Commercial	Industrial	Units
TJ	Junction temperature		0 to 85 ²	-40 to 100 ²	°C
VCC ³	1.5 V DC core supply volta	ge	1.425 to 1.575	1.425 to 1.575	V
VJTAG	JTAG DC voltage		1.4 to 3.6	1.4 to 3.6	V
VPUMP	Programming voltage	Programming Mode	3.15 to 3.45	3.15 to 3.45	V
		Operation ⁴	0 to 3.6	0 to 3.6	V
VCCPLL	Analog power supply (PLL))	1.425 to 1.575	1.425 to 1.575	V
VCCI and VMV ⁵	1.5 V DC supply voltage		1.425 to 1.575	1.425 to 1.575	V
	1.8 V DC supply voltage		1.7 to 1.9	1.7 to 1.9	V
	2.5 V DC supply voltage		2.3 to 2.7	2.3 to 2.7	V
	3.3 V DC supply voltage		3.0 to 3. <u>6</u>	3.0 to 3. <u>6</u>	V
	3.3 V wide range DC suppl	ly voltage ⁶	2.7 to 3.6	2.7 to 3.6	V
	LVDS/B-LVDS/M-LVDS diff	ferential I/O	2.375 to 2.625	2.375 to 2.625	V
	LVPECL differential I/O		3.0 to 3.6	3.0 to 3.6	V

Notes:

1. All parameters representing voltages are measured with respect to GND unless otherwise specified.

- 2. Software Default Junction Temperature Range in the Libero[®] System-on-Chip (SoC) software is set to 0°C to +70°C for commercial, and -40°C to +85°C for industrial. To ensure targeted reliability standards are met across the full range of junction temperatures, Microsemi recommends using custom settings for temperature range before running timing and power analysis tools. For more information regarding custom settings, refer to the New Project Dialog Box in the Libero SoC Online Help.
- 3. The ranges given here are for power supplies only. The recommended input voltage ranges specific to each I/O standard are given in Table 2-18 on page 2-19.
- 4. VPUMP can be left floating during operation (not programming mode).
- 5. VMV and VCCI should be at the same voltage within a given I/O bank. VMV pins must be connected to the corresponding VCCI pins. See the "VMVx I/O Supply Voltage (quiet)" section on page 3-1 for further information.
- 6. 3.3 V wide range is compliant to the JESD8-B specification and supports 3.0 V VCCI operation.



Overview of I/O Performance

Summary of I/O DC Input and Output Levels – Default I/O Software Settings

Table 2-18 • Summary of Maximum and Minimum DC Input and Output Levels Applicable to Commercial and Industrial Conditions—Software Default Settings Applicable to Advanced I/O Banks

		Equiv.			VIL	VIH		VOL	VOH		
I/O Standard	Drive Strength	Software Default Drive Strength Option ²	Slew Rate	Min V	Max V	Min V	Max V	Max V	Min V	IOL ¹ mA	IOH ¹ mA
3.3 V LVTTL / 3.3 V LVCMOS	12 mA	12 mA	High	-0.3	0.8	2	3.6	0.4	2.4	12	12
3.3 V LVCMOS Wide Range ³	100 µA	12 mA	High	-0.3	0.8	2	3.6	0.2	VCCI – 0.2	0.1	0.1
2.5 V LVCMOS	12 mA	12 mA	High	-0.3	0.7	1.7	2.7	0.7	1.7	12	12
1.8 V LVCMOS	12 mA	12 mA	High	-0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI – 0.45	12	12
1.5 V LVCMOS	12 mA	12 mA	High	-0.3	0.35 * VCCI	0.65 * VCCI	1.6	0.25 * VCCI	0.75 * VCCI	12	12
3.3 V PCI		Per PCI specifications									
3.3 V PCI-X		Per PCI-X specifications									

Notes:

1. Currents are measured at 85°C junction temperature.

2. 3.3 V LVCMOS wide range is applicable to 100 μA drive strength only. The configuration will NOT operate at the equivalent software default drive strength. These values are for Normal Ranges ONLY.

3. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.



Table 2-30 • I/O Output Buffer Maximum Resistances¹ Applicable to Standard I/O Banks

Standard	Drive Strength	R _{PULL-DOWN} (Ω) ²	R _{PULL-UP} (Ω) ³
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
3.3 V LVCMOS Wide Range ⁴	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
1.5 V LVCMOS	2 mA	200	224

Notes:

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at http://www.microsemi.com/soc/download/ibis/default.aspx.

2. R_(PULL-DOWN-MAX) = (VOLspec) / IOLspec

3. R_(PULL-UP-MAX) = (VCCImax – VOHspec) / IOHspec

4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances Minimum and Maximum Weak Pull-Up/Pull-Down Resistance Values

	R _{(WEAK}	PULL-UP) ¹ Ω)	R _{(WEAK P}	ull-down) ² Ω)
VCCI	Min	Мах	Min	Мах
3.3 V	10 k	45 k	10 k	45 k
3.3 V (wide range I/Os)	10 k	45 k	10 k	45 k
2.5 V	11 k	55 k	12 k	74 k
1.8 V	18 k	70 k	17 k	110 k
1.5 V	19 k	90 k	19 k	140 k

Notes:

R_(WEAK PULL-UP-MAX) = (VCCI_{MAX} - VOH_{spec}) / I_(WEAK PULL-UP-MIN)
 R_(WEAK PULL-DOWN-MAX) = (VOL_{spec}) / I_(WEAK PULL-DOWN-MIN)



	Drive Strength	IOSL (mA) ¹	IOSH (mA) ¹
3.3 V LVTTL / 3.3 V LVCMOS	2 mA	27	25
	4 mA	27	25
	6 mA	54	51
	8 mA	54	51
	12 mA	109	103
	16 mA	127	132
	24 mA	181	268
3.3 V LVCMOS Wide Range ²	100 µA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	18	16
	4 mA	18	16
	6 mA	37	32
	8 mA	37	32
	12 mA	74	65
	16 mA	87	83
	24 mA	124	169
1.8 V LVCMOS	2 mA	11	9
	4 mA	22	17
	6 mA	44	35
	8 mA	51	45
	12 mA	74	91
	16 mA	74	91
1.5 V LVCMOS	2 mA	16	13
	4 mA	33	25
	6 mA	39	32
	8 mA	55	66
	12 mA	55	66
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	109	103

) Microsemi.

Power Matters."

Notes:

1. $T_J = 100^{\circ}C$

Applicable to 3.3 V LVCMOS Wide Range. I_{OSL}/I_{OSH} dependent on the I/O buffer drive strength selected for wide range applications. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.



3.3 V LVCMOS Wide Range

Table 2-47 • Minimum and Maximum DC Input and Output Levels Applicable to Advanced I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software Default	v	11	v	ІН	VOI	УОН	101	юн	IOSI	IOSH	JII 2	IIH3
Drive Strength	Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	μ Α 5	μA ⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.2	VDD - 0.2	100	100	51	54	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.2	VDD - 0.2	100	100	103	109	10	10
100 µA	16 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	132	127	10	10
100 µA	24 mA	-0.3	0.8	2	3.6	0.2	VDD - 0.2	100	100	268	181	10	10

Notes:

 The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

4. Currents are measured at 85°C junction temperature.

5. All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

6. Software default selection highlighted in gray.

Table 2-48 • Minimum and Maximum DC Input and Output Levels Applicable to Standard Plus I/O Banks

3.3 V LVCMOS Wide Range	Equiv. Software	Equiv. Software VIL VIH VOL		VOH	IOL	ЮН	IOSL	IOSH	IIL²	IIH ³			
Drive Strength	Default Drive Strength Option ¹	Min V	Max V	Min V	Max V	Max V	Min V	μA	μA	Max mA ⁴	Max mA ⁴	µA⁵	μA⁵
100 µA	2 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	4 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	25	27	10	10
100 µA	6 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	8 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	51	54	10	10
100 µA	12 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10
100 μA	16 mA	-0.3	0.8	2	3.6	0.2	VDD – 0.2	100	100	103	109	10	10

Notes:

 The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is ±100 μA. Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.

2. IIL is the input leakage current per I/O pin over recommended operation conditions where –0.3 V < VIN < VIL.

3. IIH is the input leakage current per I/O pin over recommended operating conditions VIH < VIN < VCCI. Input current is larger when operating outside recommended ranges

4. Currents are measured at 85°C junction temperature.

5. All LVMCOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

6. Software default selection highlighted in gray.



Timing Characteristics

Table 2-60 • 2.5 V LVCMOS High Slew

Commercial-Case Conditions: $T_J = 70^{\circ}$ C, Worst-Case VCC = 1.425 V, Worst-Case VCCI = 2.3 V Applicable to Advanced I/O Banks

Drive Strength	Speed Grade	t _{DOUT}	t _{DP}	t _{DIN}	t _{PY}	t _{EOUT}	t _{zL}	t _{zH}	t _{LZ}	t _{HZ}	t _{zLS}	t _{zHS}	Units
4 mA	Std.	0.60	8.66	0.04	1.31	0.43	7.83	8.66	2.68	2.30	10.07	10.90	ns
	-1	0.51	7.37	0.04	1.11	0.36	6.66	7.37	2.28	1.96	8.56	9.27	ns
	-2	0.45	6.47	0.03	0.98	0.32	5.85	6.47	2.00	1.72	7.52	8.14	ns
6 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	-1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	-2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
8 mA	Std.	0.60	5.17	0.04	1.31	0.43	5.04	5.17	3.05	3.00	7.27	7.40	ns
	-1	0.51	4.39	0.04	1.11	0.36	4.28	4.39	2.59	2.55	6.19	6.30	ns
	-2	0.45	3.86	0.03	0.98	0.32	3.76	3.86	2.28	2.24	5.43	5.53	ns
12 mA	Std.	0.60	3.56	0.04	1.31	0.43	3.63	3.43	3.30	3.44	5.86	5.67	ns
	-1	0.51	3.03	0.04	1.11	0.36	3.08	2.92	2.81	2.92	4.99	4.82	ns
	-2	0.45	2.66	0.03	0.98	0.32	2.71	2.56	2.47	2.57	4.38	4.23	ns
16 mA	Std.	0.60	3.35	0.04	1.31	0.43	3.41	3.06	3.36	3.55	5.65	5.30	ns
	-1	0.51	2.85	0.04	1.11	0.36	2.90	2.60	2.86	3.02	4.81	4.51	ns
	-2	0.45	2.50	0.03	0.98	0.32	2.55	2.29	2.51	2.65	4.22	3.96	ns
24 mA	Std.	0.60	3.09	0.04	1.31	0.43	3.15	2.44	3.44	4.00	5.38	4.68	ns
	-1	0.51	2.63	0.04	1.11	0.36	2.68	2.08	2.92	3.40	4.58	3.98	ns
	-2	0.45	2.31	0.03	0.98	0.32	2.35	1.82	2.57	2.98	4.02	3.49	ns

Notes:

1. Software default selection highlighted in gray.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



B-LVDS/M-LVDS

Bus LVDS (B-LVDS) and Multipoint LVDS (M-LVDS) specifications extend the existing LVDS standard to highperformance multipoint bus applications. Multidrop and multipoint bus configurations may contain any combination of drivers, receivers, and transceivers. Microsemi LVDS drivers provide the higher drive current required by B-LVDS and M-LVDS to accommodate the loading. The drivers require series terminations for better signal quality and to control voltage swing. Termination is also required at both ends of the bus since the driver can be located anywhere on the bus. These configurations can be implemented using the TRIBUF_LVDS and BIBUF_LVDS macros along with appropriate terminations. Multipoint designs using Microsemi LVDS macros can achieve up to 200 MHz with a maximum of 20 loads. A sample application is given in Figure 2-13. The input and output buffer delays are available in the LVDS section in Table 2-92.

Example: For a bus consisting of 20 equidistant loads, the following terminations provide the required differential voltage, in worst-case Industrial operating conditions, at the farthest receiver: $R_S = 60 \Omega$ and $R_T = 70 \Omega$, given $Z_0 = 50 \Omega$ (2") and $Z_{stub} = 50 \Omega$ (~1.5").





LVPECL

Low-Voltage Positive Emitter-Coupled Logic (LVPECL) is another differential I/O standard. It requires that one data bit be carried through two signal lines. Like LVDS, two pins are needed. It also requires external resistor termination.

The full implementation of the LVDS transmitter and receiver is shown in an example in Figure 2-14. The building blocks of the LVPECL transmitter-receiver are one transmitter macro, one receiver macro, three board resistors at the transmitter end, and one resistor at the receiver end. The values for the three driver resistors are different from those used in the LVDS implementation because the output standard specifications are different.











Figure 2-16 • Timing Model of the Registered I/O Buffers with Synchronous Enable and Asynchronous Clear



Timing Characteristics

Table 2-107 • A3P015 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

		-	-2	-	-1	S	td.	
Parameter	Description	Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	0.66	0.81	0.75	0.92	0.88	1.08	ns
t _{RCKH}	Input High Delay for Global Clock	0.67	0.84	0.76	0.96	0.89	1.13	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.18		0.21		0.25	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage-supply levels, refer to Table 2-6 on page 2-6 for derating values.

Table 2-108 • A3P030 Global Resource

Commercial-Case Conditions: T_J = 70°C, VCC = 1.425 V

		-	-2	-	-1	S	td.	
Parameter	Description	Min. ¹	Max. ²	Min. ¹	Max. ²	Min. ¹	Max. ²	Units
t _{RCKL}	Input Low Delay for Global Clock	0.67	0.81	0.76	0.92	0.89	1.09	ns
^t _{RCKH}	Input High Delay for Global Clock	0.68	0.85	0.77	0.97	0.91	1.14	ns
t _{RCKMPWH}	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
t _{RCKMPWL}	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
t _{RCKSW}	Maximum Skew for Global Clock		0.18		0.21		0.24	ns

Notes:

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).

2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).

3. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



Timing Waveforms







Figure 2-32 • RAM Read for Pipelined Output. Applicable to Both RAM4K9 and RAM512x18.



Timing Characteristics

Table 2-116 • RAM4K9

Commercial-Case Conditions: T_J = 70°C, Worst-Case VCC = 1.425 V

Parameter	Description	-2	-1	Std.	Units
t _{AS}	Address setup time	0.25	0.28	0.33	ns
t _{AH}	Address hold time	0.00	0.00	0.00	ns
t _{ENS}	REN, WEN setup time	0.14	0.16	0.19	ns
t _{ENH}	REN, WEN hold time	0.10	0.11	0.13	ns
t _{BKS}	BLK setup time	0.23	0.27	0.31	ns
t _{BKH}	BLK hold time	0.02	0.02	0.02	ns
t _{DS}	Input data (DIN) setup time	0.18	0.21	0.25	ns
t _{DH}	Input data (DIN) hold time	0.00	0.00	0.00	ns
t _{CKQ1}	Clock High to new data valid on DOUT (output retained, WMODE = 0)	2.36	2.68	3.15	ns
	Clock High to new data valid on DOUT (flow-through, WMODE = 1)	1.79	2.03	2.39	ns
t _{CKQ2}	Clock High to new data valid on DOUT (pipelined)	0.89	1.02	1.20	ns
t _{C2CWWL} 1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Closing Edge	0.33	0.28	0.25	ns
t _{C2CWWH} 1	Address collision clk-to-clk delay for reliable write after write on same address—Applicable to Rising Edge	0.30	0.26	0.23	ns
t _{C2CRWH} 1	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.45	0.38	0.34	ns
t _{C2CWRH} 1	Address collision clk-to-clk delay for reliable write access after read on same address— Applicable to Opening Edge	0.49	0.42	0.37	ns
t _{RSTBQ}	RESET Low to data out Low on DOUT (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on DOUT (pipelined)	0.92	1.05	1.23	ns
t _{REMRSTB}	RESET removal	0.29	0.33	0.38	ns
t _{RECRSTB}	RESET recovery	1.50	1.71	2.01	ns
t _{MPWRSTB}	RESET minimum pulse width	0.21	0.24	0.29	ns
t _{CYC}	Clock cycle time	3.23	3.68	4.32	ns
F _{MAX}	Maximum frequency	310	272	231	MHz

Notes:

1. For more information, refer to the application note Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs.

2. For specific junction temperature and voltage supply levels, refer to Table 2-6 on page 2-6 for derating values.



CS121				
Pin Number	A3P060 Function			
K10	VPUMP			
K11	GDB1/IO47RSB0			
L1	VMV1			
L2	GNDQ			
L3	IO65RSB1			
L4	IO63RSB1			
L5	IO61RSB1			
L6	IO58RSB1			
L7	IO57RSB1			
L8	IO55RSB1			
L9	GNDQ			
L10	GDA0/IO50RSB0			
L11 VMV1				



Package Pin Assignments

PQ208 – Top View



Note

For more information on package drawings, see PD3068: Package Mechanical Drawings.

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Package Pin Assignments

	PQ208		PQ208	PQ208	
Pin Number	A3P1000 Function	Pin Number	A3P1000 Function	Pin Number	A3P1000 Function
109	TRST	145	IO84PDB1	181	IO33RSB0
110	VJTAG	146	IO82NDB1	182	IO31RSB0
111	GDA0/IO113NDB1	147	IO82PDB1	183	IO29RSB0
112	GDA1/IO113PDB1	148	IO80NDB1	184	IO27RSB0
113	GDB0/IO112NDB1	149	GBC2/IO80PDB1	185	IO25RSB0
114	GDB1/IO112PDB1	150	IO79NDB1	186	VCCIB0
115	GDC0/IO111NDB1	151	GBB2/IO79PDB1	187	VCC
116	GDC1/IO111PDB1	152	IO78NDB1	188	IO22RSB0
117	IO109NDB1	153	GBA2/IO78PDB1	189	IO20RSB0
118	IO109PDB1	154	VMV1	190	IO18RSB0
119	IO106NDB1	155	GNDQ	191	IO16RSB0
120	IO106PDB1	156	GND	192	IO15RSB0
121	IO104PSB1	157	VMV0	193	IO14RSB0
122	GND	158	GBA1/IO77RSB0	194	IO13RSB0
123	VCCIB1	159	GBA0/IO76RSB0	195	GND
124	IO99NDB1	160	GBB1/IO75RSB0	196	IO12RSB0
125	IO99PDB1	161	GBB0/IO74RSB0	197	IO11RSB0
126	NC	162	GND	198	IO10RSB0
127	IO96NDB1	163	GBC1/IO73RSB0	199	IO09RSB0
128	GCC2/IO96PDB1	164	GBC0/IO72RSB0	200	VCCIB0
129	GCB2/IO95PSB1	165	IO70RSB0	201	GAC1/IO05RSB0
130	GND	166	IO67RSB0	202	GAC0/IO04RSB0
131	GCA2/IO94PSB1	167	IO63RSB0	203	GAB1/IO03RSB0
132	GCA1/IO93PDB1	168	IO60RSB0	204	GAB0/IO02RSB0
133	GCA0/IO93NDB1	169	IO57RSB0	205	GAA1/IO01RSB0
134	GCB0/IO92NDB1	170	VCCIB0	206	GAA0/IO00RSB0
135	GCB1/IO92PDB1	171	VCC	207	GNDQ
136	GCC0/IO91NDB1	172	IO54RSB0	208	VMV0
137	GCC1/IO91PDB1	173	IO51RSB0		
138	IO88NDB1	174	IO48RSB0		
139	IO88PDB1	175	IO45RSB0		
140	VCCIB1	176	IO42RSB0		
141	GND	177	IO40RSB0		
142	VCC	178	GND		
143	IO86PSB1	179	IO38RSB0		
144	IO84NDB1	180	IO35RSB0		

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Package Pin Assignments

FG144			FG144	FG144	
Pin Number	A3P600 Function	Pin Number	A3P600 Function	Pin Number	A3P600 Function
A1	GNDQ	D1	IO169PDB3	G1	GFA1/IO162PPB3
A2	VMV0	D2	IO169NDB3	G2	GND
A3	GAB0/IO02RSB0	D3	IO172NDB3	G3	VCCPLF
A4	GAB1/IO03RSB0	D4	GAA2/IO174PPB3	G4	GFA0/IO162NPB3
A5	IO10RSB0	D5	GAC0/IO04RSB0	G5	GND
A6	GND	D6	GAC1/IO05RSB0	G6	GND
A7	IO34RSB0	D7	GBC0/IO54RSB0	G7	GND
A8	VCC	D8	GBC1/IO55RSB0	G8	GDC1/IO86PPB1
A9	IO50RSB0	D9	GBB2/IO61PDB1	G9	IO74NDB1
A10	GBA0/IO58RSB0	D10	IO61NDB1	G10	GCC2/IO74PDB1
A11	GBA1/IO59RSB0	D11	IO62NPB1	G11	IO73NDB1
A12	GNDQ	D12	GCB1/IO70PPB1	G12	GCB2/IO73PDB1
B1	GAB2/IO173PDB3	E1	VCC	H1	VCC
B2	GND	E2	GFC0/IO164NDB3	H2	GFB2/IO160PDB3
B3	GAA0/IO00RSB0	E3	GFC1/IO164PDB3	H3	GFC2/IO159PSB3
B4	GAA1/IO01RSB0	E4	VCCIB3	H4	GEC1/IO146PDB3
B5	IO13RSB0	E5	IO174NPB3	H5	VCC
B6	IO19RSB0	E6	VCCIB0	H6	IO80PDB1
B7	IO31RSB0	E7	VCCIB0	H7	IO80NDB1
B8	IO39RSB0	E8	GCC1/IO69PDB1	H8	GDB2/IO90RSB2
B9	GBB0/IO56RSB0	E9	VCCIB1	H9	GDC0/IO86NPB1
B10	GBB1/IO57RSB0	E10	VCC	H10	VCCIB1
B11	GND	E11	GCA0/IO71NDB1	H11	IO84PSB1
B12	VMV1	E12	IO72NDB1	H12	VCC
C1	IO173NDB3	F1	GFB0/IO163NPB3	J1	GEB1/IO145PDB3
C2	GFA2/IO161PPB3	F2	VCOMPLF	J2	IO160NDB3
C3	GAC2/IO172PDB3	F3	GFB1/IO163PPB3	J3	VCCIB3
C4	VCC	F4	IO161NPB3	J4	GEC0/IO146NDB3
C5	IO16RSB0	F5	GND	J5	IO129RSB2
C6	IO25RSB0	F6	GND	J6	IO131RSB2
C7	IO28RSB0	F7	GND	J7	VCC
C8	IO42RSB0	F8	GCC0/IO69NDB1	J8	ТСК
C9	IO45RSB0	F9	GCB0/IO70NPB1	J9	GDA2/IO89RSB2
C10	GBA2/IO60PDB1	F10	GND	J10	TDO
C11	IO60NDB1	F11	GCA1/IO71PDB1	J11	GDA1/IO88PDB1
C12	GBC2/IO62PPB1	F12	GCA2/IO72PDB1	J12	GDB1/IO87PDB1



	FG484	FG484		FG484	
Pin Number	A3P600 Function	Pin Number	A3P600 Function	Pin Number	A3P600 Function
K19	IO75NDB1	M11	GND	P3	IO153NDB3
K20	NC	M12	GND	P4	IO159NDB3
K21	IO76NDB1	M13	GND	P5	IO156NPB3
K22	IO76PDB1	M14	VCC	P6	IO151PPB3
L1	NC	M15	GCB2/IO73PPB1	P7	IO158PPB3
L2	IO155PDB3	M16	GCA1/IO71PPB1	P8	VCCIB3
L3	NC	M17	GCC2/IO74PPB1	P9	GND
L4	GFB0/IO163NPB3	M18	IO80PPB1	P10	VCC
L5	GFA0/IO162NDB3	M19	GCA2/IO72PDB1	P11	VCC
L6	GFB1/IO163PPB3	M20	IO79PPB1	P12	VCC
L7	VCOMPLF	M21	IO78PPB1	P13	VCC
L8	GFC0/IO164NPB3	M22	NC	P14	GND
L9	VCC	N1	IO154NDB3	P15	VCCIB1
L10	GND	N2	IO154PDB3	P16	GDB0/IO87NPB1
L11	GND	N3	NC	P17	IO85NDB1
L12	GND	N4	GFC2/IO159PDB3	P18	IO85PDB1
L13	GND	N5	IO161NPB3	P19	IO84PDB1
L14	VCC	N6	IO156PPB3	P20	NC
L15	GCC0/IO69NPB1	N7	IO129RSB2	P21	IO81PDB1
L16	GCB1/IO70PPB1	N8	VCCIB3	P22	NC
L17	GCA0/IO71NPB1	N9	VCC	R1	NC
L18	IO67NPB1	N10	GND	R2	NC
L19	GCB0/IO70NPB1	N11	GND	R3	VCC
L20	IO77PDB1	N12	GND	R4	IO150PDB3
L21	IO77NDB1	N13	GND	R5	IO151NPB3
L22	IO78NPB1	N14	VCC	R6	IO147NPB3
M1	NC	N15	VCCIB1	R7	GEC0/IO146NPB3
M2	IO155NDB3	N16	IO73NPB1	R8	VMV3
M3	IO158NPB3	N17	IO80NPB1	R9	VCCIB2
M4	GFA2/IO161PPB3	N18	IO74NPB1	R10	VCCIB2
M5	GFA1/IO162PDB3	N19	IO72NDB1	R11	IO117RSB2
M6	VCCPLF	N20	NC	R12	IO110RSB2
M7	IO160NDB3	N21	IO79NPB1	R13	VCCIB2
M8	GFB2/IO160PDB3	N22	NC	R14	VCCIB2
M9	VCC	P1	NC	R15	VMV2
M10	GND	P2	IO153PDB3	R16	IO94RSB2

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Package Pin Assignments

FG484				
Pin Number	A3P1000 Function			
Y15	VCC			
Y16	NC			
Y17	NC			
Y18	GND			
Y19	NC			
Y20	NC			
Y21	NC			
Y22	VCCIB1			
AA1	GND			
AA2	VCCIB3			
AA3	NC			
AA4	IO181RSB2			
AA5	IO178RSB2			
AA6	IO175RSB2			
AA7	IO169RSB2			
AA8	IO166RSB2			
AA9	IO160RSB2			
AA10	IO152RSB2			
AA11	IO146RSB2			
AA12	IO139RSB2			
AA13	IO133RSB2			
AA14	NC			
AA15	NC			
AA16	IO122RSB2			
AA17	IO119RSB2			
AA18	IO117RSB2			
AA19	NC			
AA20	NC			
AA21	VCCIB1			
AA22	GND			
AB1	GND			
AB2	GND			
AB3	VCCIB2			
AB4 IO180RSB2				
AB5 IO176RSB2				
AB6	IO173RSB2			

FG484				
Pin Number	A3P1000 Function			
AB7	IO167RSB2			
AB8	IO162RSB2			
AB9	IO156RSB2			
AB10	IO150RSB2			
AB11	IO145RSB2			
AB12	IO144RSB2			
AB13	IO132RSB2			
AB14	IO127RSB2			
AB15	IO126RSB2			
AB16	IO123RSB2			
AB17	IO121RSB2			
AB18	IO118RSB2			
AB19	NC			
AB20	VCCIB2			
AB21	GND			
AB22 GND				



Datasheet Information

Revision	Changes	Page
Revision 10 (continued)	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-28 • I/O Output Buffer Maximum Resistances1 through Table 2-30 • I/O Output Buffer Maximum Resistances1 was replaced by "Same as regular 3.3 V" (SAR 33852).	2-26 to 2-28
	The equations in the notes for Table 2-31 • I/O Weak Pull-Up/Pull-Down Resistances were corrected (SAR 32470).	2-28
	"TBD" for 3.3 V LVCMOS Wide Range in Table 2-32 • I/O Short Currents IOSH/IOSL through Table 2-34 • I/O Short Currents IOSH/IOSL was replaced by "Same as regular 3.3 V LVCMOS" (SAR 33852).	2-29 to 2-31
	In the "3.3 V LVCMOS Wide Range" section, values were added to Table 2-47 through Table 2-49 for IOSL and IOSH, replacing "TBD" (SAR 33852).	2-39 to 2-40
	The following sentence was deleted from the "2.5 V LVCMOS" section (SAR 24916): "It uses a 5 V-tolerant input buffer and push-pull output buffer."	2-47
	The table notes were revised for Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels (SAR 33859).	2-66
	Values were added for $F_{DDRIMAX}$ and F_{DDOMAX} in Table 2-102 • Input DDR Propagation Delays and Table 2-104 • Output DDR Propagation Delays (SAR 23919).	2-78, 2-80
	Table 2-115 • ProASIC3 CCC/PLL Specification was updated. A note was added to indicate that when the CCC/PLL core is generated by Microsemi core generator software, not all delay values of the specified delay increments are available (SAR 25705).	2-90
	The following figures were deleted (SAR 29991). Reference was made to a new application note, <i>Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs</i> , which covers these cases in detail (SAR 21770).	2-92
	Figure 2-34 • Write Access after Write onto Same Address	2-92, 2-94,
	Figure 2-35 • Read Access after Write onto Same Address	2-99 2-102
	Figure 2-35 • Read Access after Write onto Same Address	
	Characteristics" tables, Figure 2-39 • FIFO Reset, and the FIFO "Timing Characteristics" tables were revised to ensure consistency with the software names (SARs 29991, 30510).	
	The "Pin Descriptions" chapter has been added (SAR 21642).	3-1
	Package names used in the "Package Pin Assignments" section were revised to match standards given in <i>Package Mechanical Drawings</i> (SAR 27395).	4-1
July 2010	The versioning system for datasheets has been changed. Datasheets are assigned a revision number that increments each time the datasheet is revised. The "ProASIC3 Device Status" table on page IV indicates the status for each device in the device family.	N/A